

INJ021AAP1

High Speed Switching
Silicon P-channel MOSFET

DESCRIPTION

INJ021AAP1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery, because voltage drive and low on resistance.

FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current $I_D = -1.2A$
- Drive voltage $-4.0V$
- Low on Resistance. $R_{DS(on)} = 0.7 \Omega$ (TYP).
- High speed switching.

APPLICATION

Switching

MAXIMUM RATINGS (Ta=25°C)

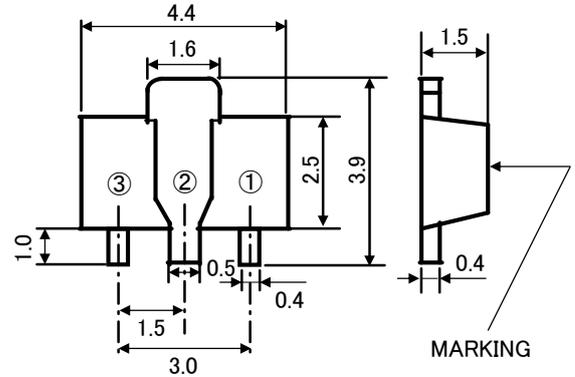
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	-100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current(DC)	I _D	-1.2	A
Drain Current(Pulse) (※1)	I _{DP}	-3	A
Total Power Dissipation	P _D	0.5	W
		1.2 (※2)	
Channel Temperature	T _{ch}	+150	°C
Storage Temperature	T _{stg}	-55~+150	°C

※1: Single pulse, $P_w \leq 1ms$

※2: package mounted on glass-epoxy substrate
(20mm × 20mm × 1mm, Cu pad 100mm²)

OUTLINE DRAWING

UNIT:mm



TERMINAL CONNECTOR

JEITA: SC-62

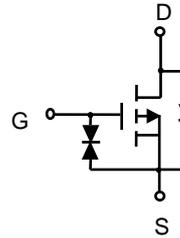
①: GATE

JEDEC: SOT-89

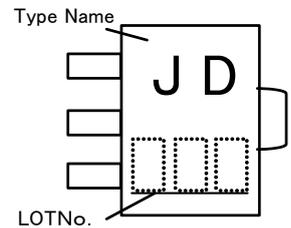
②: DRAIN

③: SOURCE

EQUIVALENT CIRCUIT



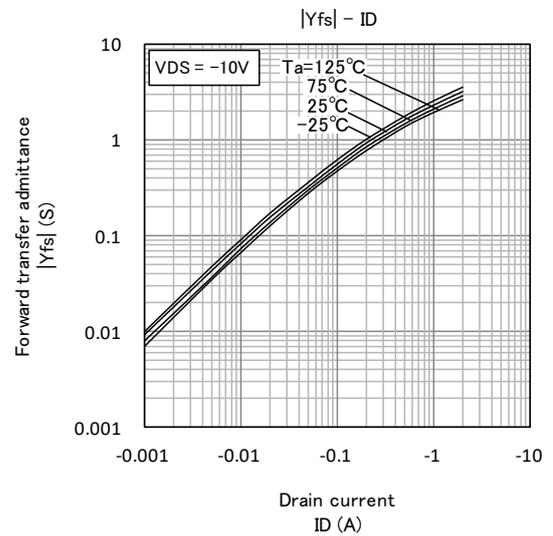
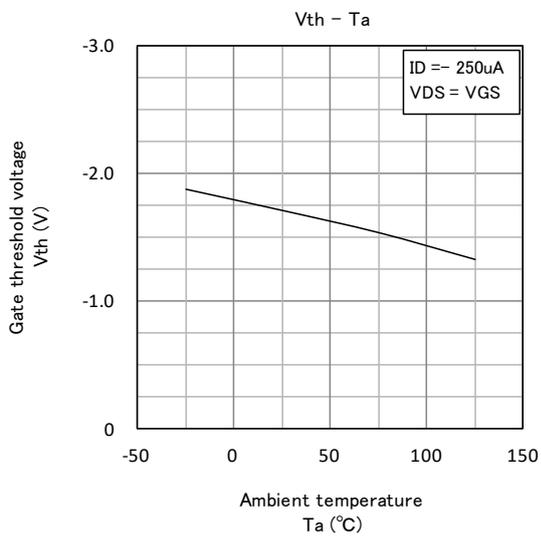
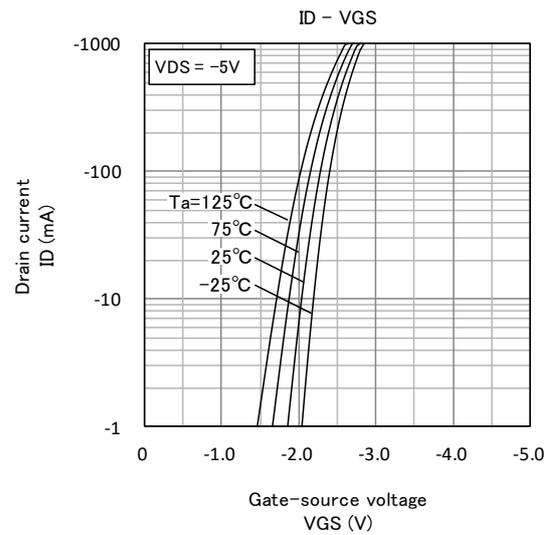
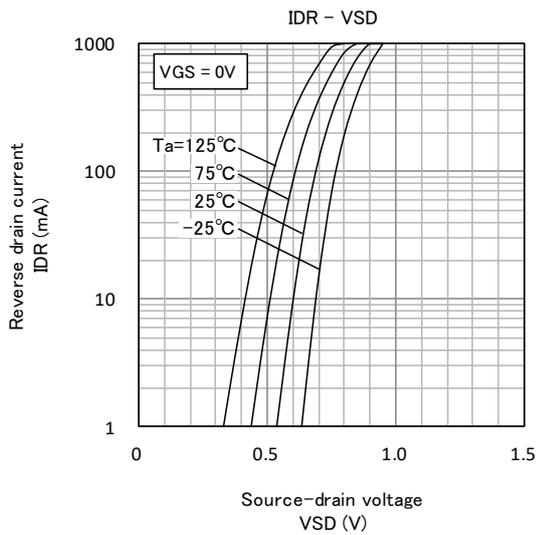
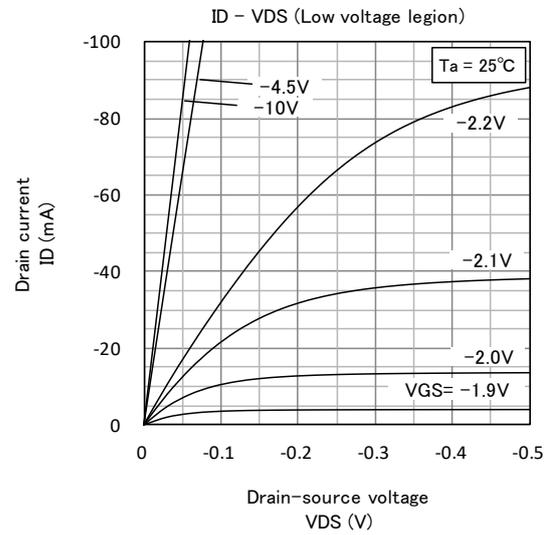
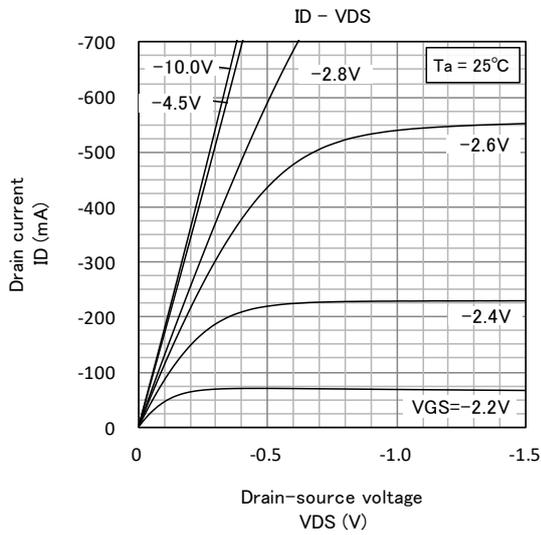
MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

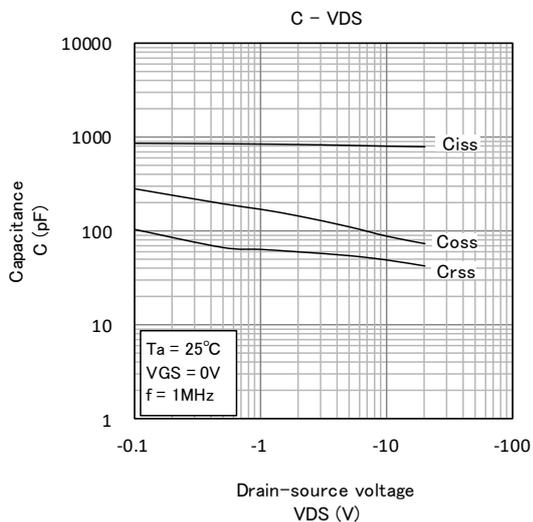
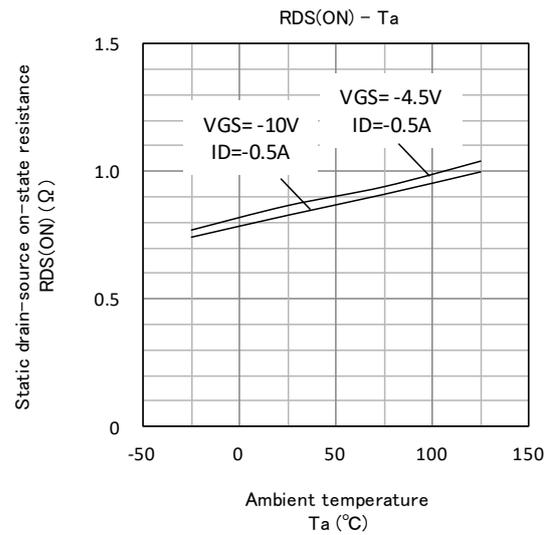
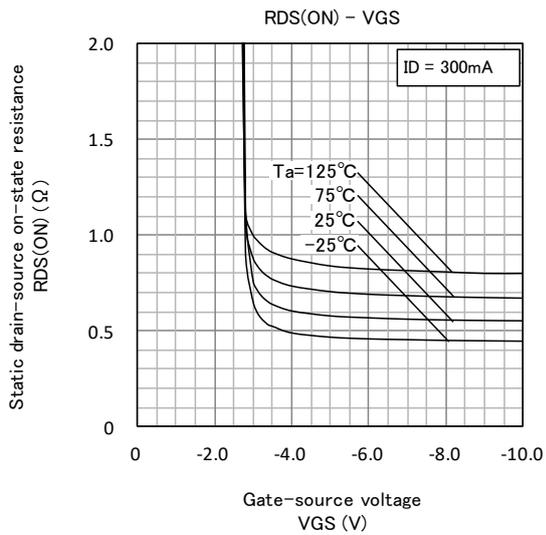
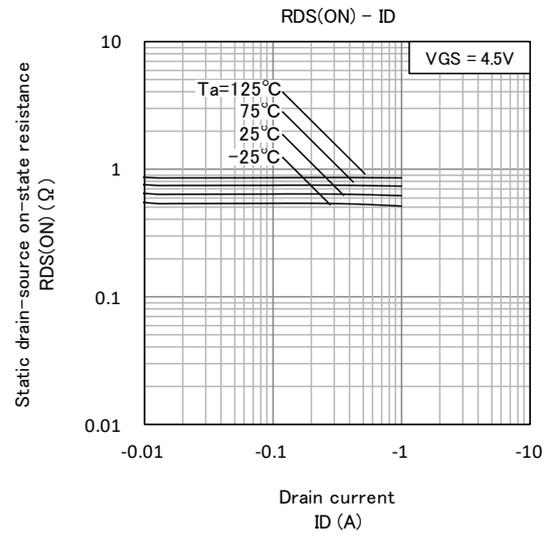
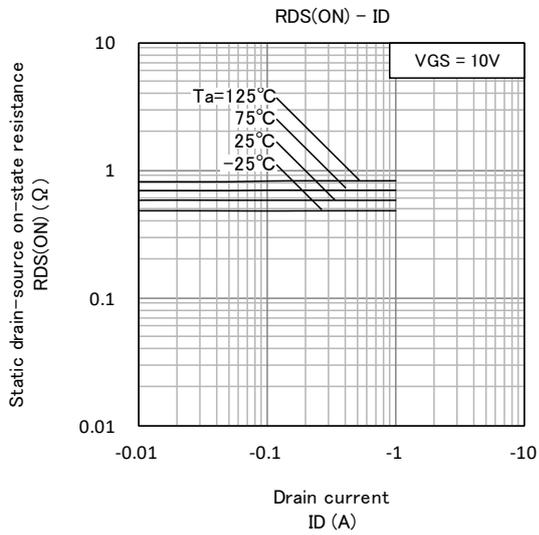
Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V(BR)DSS	$I_D = -100 \mu A, V_{GS} = 0V$	-100	-	-	V
Gate-Source Leak current	I _{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	-	-	±10	μA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -100V, V_{GS} = 0V$	-	-	-10	μA
Gate Threshold Voltage	V _{th}	$I_D = -250 \mu A, V_{DS} = V_{GS}$	-1.0	-	-2.5	V
Forward Transfer Admittance	Y _{fs}	$V_{DS} = -10V, I_D = -1A$	-	2.0	-	S
Static Drain-Source On-State Resistance	R _{DS(ON)}	$I_D = -0.5A, V_{GS} = -10V$	-	0.7	-	Ω
Input Capacitance	C _{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$	-	800	-	pF
Output Capacitance	C _{oss}		-	90	-	
Switching Time	t _{on}	$V_{DD} = -10V, I_D = -1A$	-	250	-	ns
	t _{off}	$V_{GS} = 0 \sim -5V$	-	530	-	

TYPICAL CHARACTERISTICS



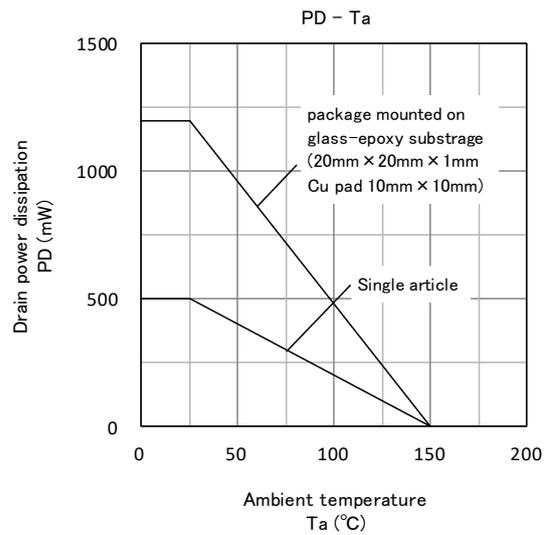
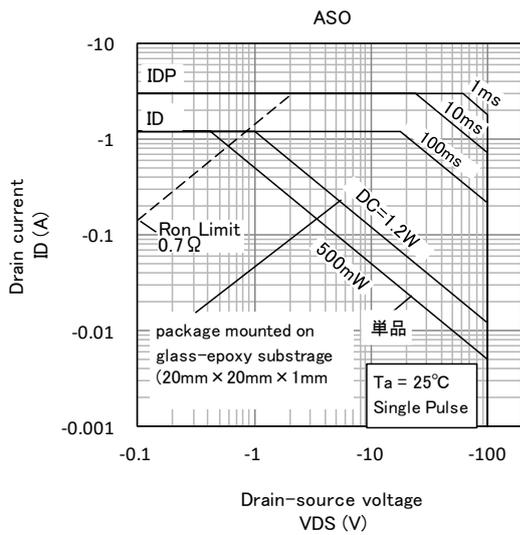
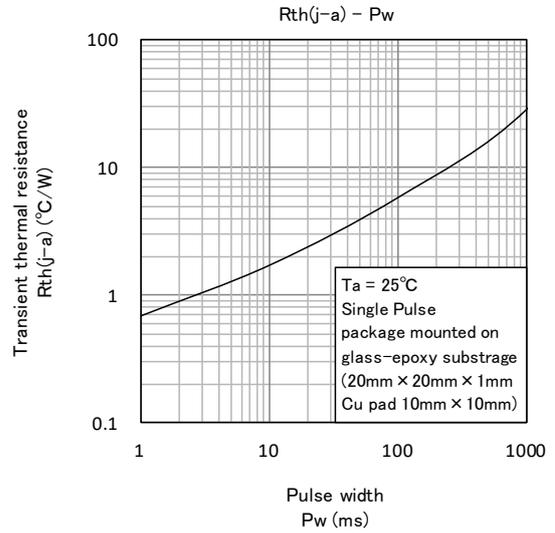
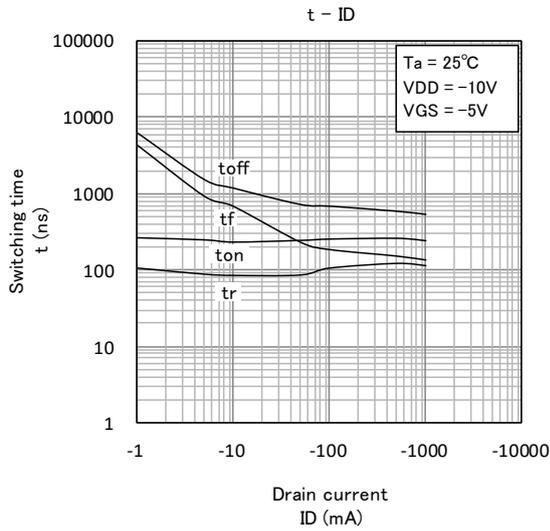
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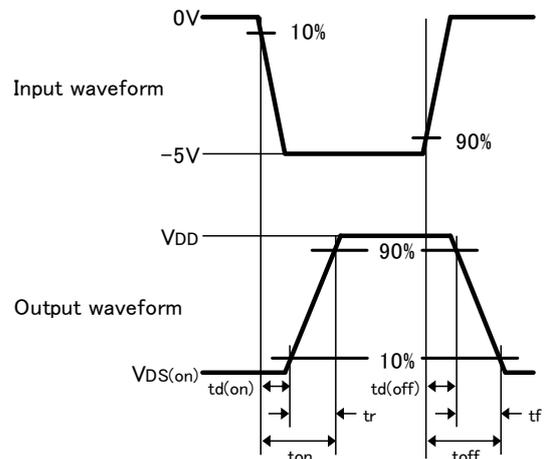
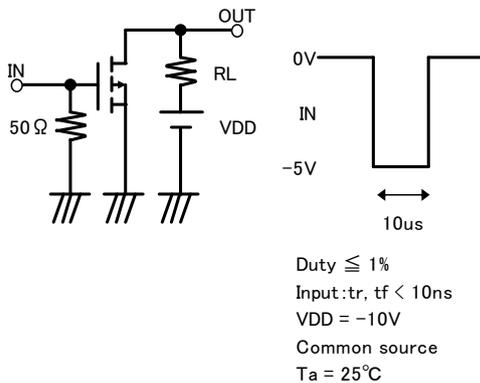


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Switching time test condition



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